TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSⅢ)

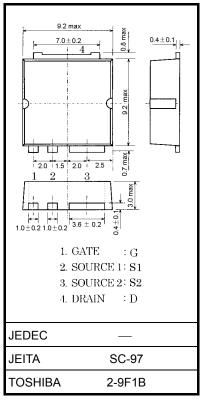
# 2SK4034

Switching Regulator, DC-DC Converter Applications Motor Drive Applications

- Low drain-source ON-resistance: R<sub>DS (ON)</sub> = 4.2 mΩ(typ.)
- High forward transfer admittance:  $|Y_{fs}| = 110 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 100 \ \mu A (V_{DS} = 60 \ V)$
- Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	60	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	60	V	
Gate-source voltage		V <sub>GSS</sub>	±20	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	75	A	
	Pulse (t $\leq$ 1 ms) (Note 1)	I <sub>DP</sub>	300		
Drain power dissipation (Tc = $25^{\circ}$ C)		PD	125	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	322	mJ	
Avalanche current		I <sub>AR</sub>	75	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	12.5	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	–55 to 150	°C	



Weight: 0.74 g (typ.)

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.0	°C/W

Note: Use the S1 pin to return the gate signal to source. Board traces should be designed so the main current flows to the S2 pin.

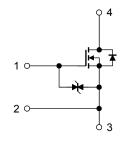
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 25 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 78  $\mu$ H, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 75 A

- Note 3: Repetitive rating: pulse width limited by maximum channel temperature
- Note 4: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Unit: mm

#### Electrical Characteristics (Note 5) (Ta = 25°C)

Ch	aracteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cui	rrent	I <sub>GSS</sub>	$V_{GS}=\pm 16~V,~V_{DS}=0~V$	_		±10	μA
Drain cut-off curr	ent	I <sub>DSS</sub>	$V_{DS} = 60 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	100	μA
Drain-source breakdown voltage		V (BR) DSS	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	60	_		V
		V (BR) DSX	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V	35	_	_	V
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	1.5	_	2.5	V
Drain-source ON-resistance		D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 38 A		4.2	5.8	mΩ
		R <sub>DS (ON)</sub>	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 38 \text{ A}$		5.5	10	mΩ
Forward transfer	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 38 \text{ A}$	55	110		S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		12400		pF
Reverse transfer capacitance		C <sub>rss</sub>			410		
Output capacitance		C <sub>oss</sub>			1100		
Switching time	Rise time	tr	$V_{GS} \stackrel{10}{_{0}} V \prod_{V} I_{D} = 38 \text{ A}$	_	15	_	
	Turn-on time	t <sub>on</sub>		_	35		
	Fall time	t <sub>f</sub>		_	45		ns
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, t <sub>w</sub> = 10 $\mu$ s	_	250		
Total gate charge (gate-source plus gate-drain)		Qg	V <sub>DD</sub> ≈ 48 V, V <sub>GS</sub> = 10 V,	_	196		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 48 \text{ V}, \text{ V}_{GS} = 10 \text{ V},$ $I_{D} = 75 \text{ A}$	_	148	_	nC
Gate-drain ("miller") charge		Q <sub>gd</sub>	1	_	48	_	

Note 5: The S1 and S2 pins should be grounded together, except when measuring the switching time.

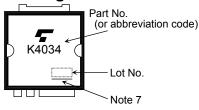
#### Source-Drain Ratings and Characteristics (Note 6) (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1, Note 6)	I <sub>DR</sub> 1	—	_	_	75	А
Pulse drain reverse current (Note 1, Note 6)	I <sub>DRP</sub> 1	—	_	_	300	А
Continuous drain reverse current (Note 1, Note 6)	I <sub>DR</sub> 2	—	_	_	1	А
Pulse drain reverse current (Note 1, Note 6)	I <sub>DRP</sub> 2	—	_	_	4	А
Forward voltage (diode)	V <sub>DS2F</sub>	I <sub>DR1</sub> = 75 A, V <sub>GS</sub> = 0 V	_	_	-1.5	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 75 A, V <sub>GS</sub> = 0 V,	_	70	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 50 A/µs	_	77		nC

Note 6: I<sub>DR</sub>1, I<sub>DRP</sub>1: Current flowing between the drain and S2 pins. Ensure that the S1 pin is left open. I<sub>DR</sub>2, I<sub>DRP</sub>2: Current flowing between the drain and S1 pins. Ensure that the S2 pin is left open.

The S1 and S2 pins should be grounded together, unless otherwise noted.

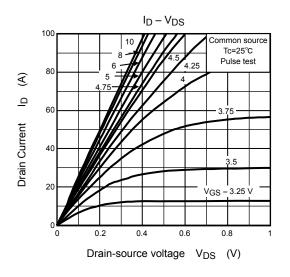
#### Marking

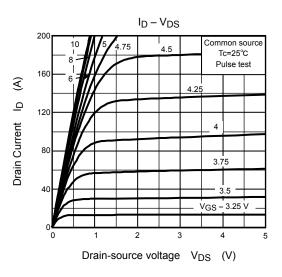


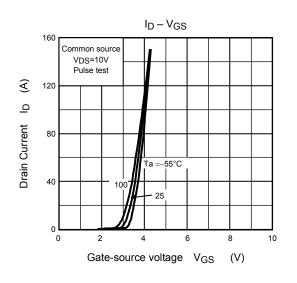
Note 7: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

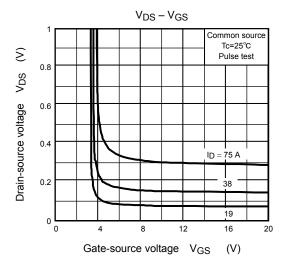
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

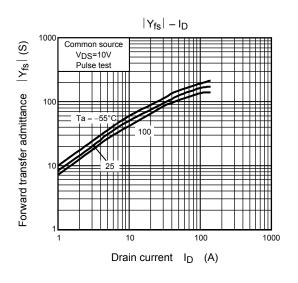
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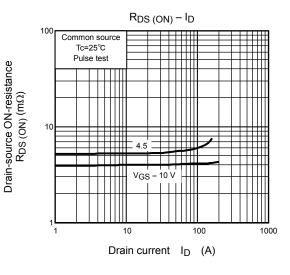




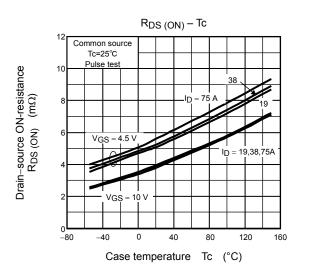


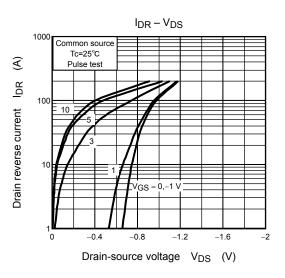


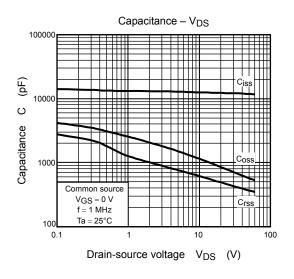


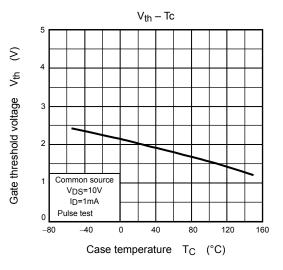


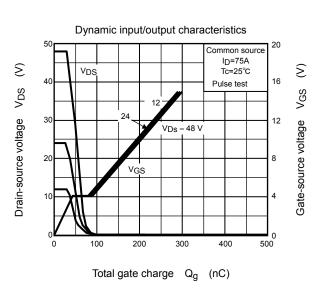
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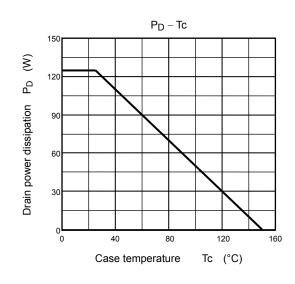


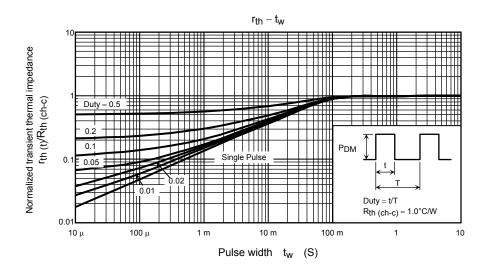




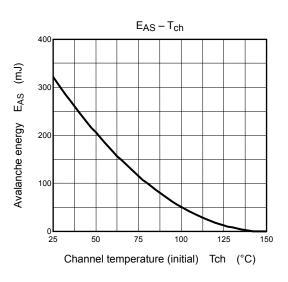


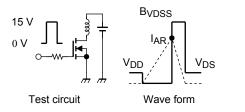






Safe operating area 1000 500 100 μs ID ma (pulsed) 300 ID max ontinuous 100 E Drain current I<sub>D</sub> 30 10 DC operation 25°C Tc : 3 \*: Single nonrepetitive pulse Tc = 25°C 0.5 Curves must be derated 0.3 linearly with increase in temperature. /nss 0.1 L 0.1 1 10 100 Drain-source voltage V<sub>DS</sub> (V)





$R_G = 25 \Omega$	$E_{AC} = \frac{1}{2} \cdot 1 \cdot 1^2$	$\left(\frac{BVDSS}{BVDSS}-VDD}\right)$
$V_{DD}=25~V,~L=78~\mu H$	LAS 2	(BVDSS-VDD)

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